

isc Silicon NPN Power Transistor

2N6560

DESCRIPTION

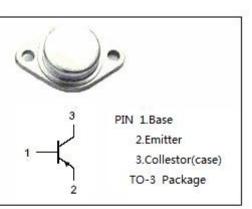
- Collector-Emitter Breakdown Voltage-: V_{CEO}=450V(Min)
- Minimum Lot-to-Lot variations for robust device Performance and reliable operation

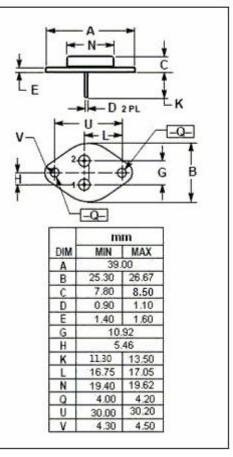
APPLICATIONS

Power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNI T
V _{CBO}	Collector-Base Voltage	450	V
V _{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage 5		v
lc	Collector Current-Continuous	10	A
PD	Collector Power Dissipation @ $T_c=25^{\circ}C$ 220		W
TJ	unction Temperature 200		°C
T _{stg}	Storage Temperature Range	-65~200	°C





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ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	мах	UNIT
V(BR)CEO	Collector-Emitter Breakdown Voltage	I _C =1mA	450			V
I _{CBO}	Collector-Base Cutoff Current	V _{CB} = 450V			1	mA
I _{EBO}	Emitter-Base Cutoff Current	V _{EB} = 5V			1	mA
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 5Α; I _B = 1Α			0.75	V
h _{FE-1}	DC Current Gain	I _C = 5A; V _{CE} = 2V	10		40	

NOTICE:

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